2N2219, 2N2219A, 2N2219AL

Small Signal Switching Transistor

NPN Silicon

Features

- MIL-PRF-19500/251 Qualified
- Available as JAN, JANTX, and JANTXV

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	75	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	800	mAdc
Total Power Dissipation @ T _A = 25°C	P _T	0.8	W
Total Power Dissipation @ T _C = 25°C	P _T	3.0	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

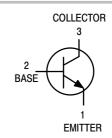
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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TO-39 CASE 205AB (2N2219, 2N2219A)



TO-5 CASE 205AA (2N2219AL)

ORDERING INFORMATION

Device	Package	Shipping		
JAN2N2219/A				
JANTX2N2219/A	TO-39	Bulk		
JANTXV2N2219/A				
JAN2N2219AL				
JANTX2N2219AL	TO-5	Bulk		
JANTXV2N2219AL				

2N2219, 2N2219A, 2N2219AL

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

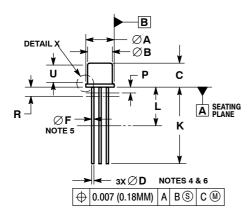
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _E = 10 mAdc)	2N2219 2N2219A/AL	V _{(BR)CEO}	30 50	- -	Vdc
Emitter-Base Cutoff Current $(V_{EB} = 5.0 \text{ Vdc})$ $(V_{EB} = 6.0 \text{ Vdc})$ $(V_{EB} = 4.0 \text{ Vdc})$	2N2219 2N2219A/AL All	I _{EBO}	- - -	10 10 10	μAdc μAdc nAdc
Collector–Emitter Cutoff Current (V _{CE} = 30 Vdc) (V _{CE} = 50 Vdc)	2N2219 2N2219A/AL	I _{CES}	- -	10 10	nAdc nAdc
Collector-Base Cutoff Current (V _{CB} = 50 Vdc) (V _{CB} = 60 Vdc) (V _{CB} = 60 Vdc) (V _{CB} = 75 Vdc) ON CHARACTERISTICS (Note 1)	2N2219 2N2219 2N2219A/AL 2N2219A/AL	I _{CBO}	- - -	10 10 10 10	nAdc μAdc nAdc μAdc
DC Current Gain		h _{FE}			_
$(I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	2N2219 2N2219A/AL 2N2219 2N2219A/AL		35 50 50 75	- 325 325	
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	2N2219 2N2219A/AL 2N2219/A/AL		75 100 100	- 300	
($I_C = 500 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$)	2N2219/A/AL		30	_) / d -
Collector – Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	2N2219 2N2219A/AL 2N2219	V _{CE(sat)}	- - -	0.4 0.3 1.6	Vdc
,	2N2219A/AL		-	1.0	
Base – Emitter Saturation Voltage $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$	2N2219 2N2219A/AL	$V_{BE(sat)}$	0.6 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	2N2219 2N2219A/AL		- -	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS					
Magnitude of Small–Signal Current Gain ($I_C = 20 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)		h _{fe}	2.5	12	_
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ kHz}$)	2N2219 2N2219A/AL	h _{fe}	50 75	- -	_
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, 100 kHz \leq f \leq 1.0 MHz)		C_{obo}	_	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I_C = 0, 100 kHz \leq f \leq 1.0 MHz)		C _{ibo}	_	25	pF
SWITCHING CHARACTERISTICS			_		
Turn-On Time (Reference Figure in MIL-PRF-19500/251)	2N2219 2N2219A/AL	t _{on}	- -	40 35	ns
Turn-Off Time (Reference Figure in MIL-PRF-19500/251)	2N2219 2N2219A/AL	t _{off}	- -	250 300	ns

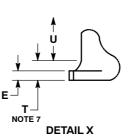
^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

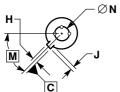
2N2219, 2N2219A, 2N2219AL

PACKAGE DIMENSIONS

TO-5 3-Lead CASE 205AA **ISSUE B**









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
 4. LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
 5. DIMENSION F. APPLIES BETWEEN DIMENSION P AND L.
 6. DIMENSION TAPPLIES BETWEEN DIMENSION LAND K.
 7. BODDY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A. B. AND T.

- SIONS A, B, AND T.

 8. DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.89	9.40	0.350	0.370	
В	8.00	8.51	0.315	0.335	
С	6.10	6.60	0.240	0.260	
D	0.41	0.53	0.016	0.021	
E	0.23	3.18	0.009	0.125	
F	0.41	0.48	0.016	0.019	
Н	0.71	0.86	0.028	0.034	
J	0.73	1.02	0.029	0.040	
K	38.10	44.45	1.500	1.750	
L	6.35		0.250		
M	45°BSC		45 °BSC		
N	5.08	BSC	0.200	0 BSC	
P		1.27		0.050	
R	1.37 BSC		0.054	BSC	
T		0.76		0.030	
U	2.54		0.100		

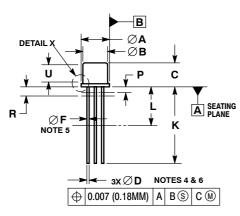
STYLE 1:

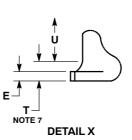
- PIN 1. EMITTER
 - BASE
 - COLLECTOR

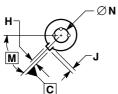
2N2219, 2N2219A, 2N2219AL

PACKAGE DIMENSIONS

TO-39 3-Lead CASE 205AB **ISSUE A**









LEAD IDENTIFICATION DETAIL

NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
- LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
- DIMENSION F APPLIES BETWEEN DIMENSION P AND L. DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
- BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A, B, AND T.
- DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.89	9.40	0.350	0.370	
В	8.00	8.51	0.315	0.335	
С	6.10	6.60	0.240	0.260	
D	0.41	0.48	0.016	0.019	
Е	0.23	3.18	0.009	0.125	
F	0.41	0.48	0.016	0.019	
Н	0.71	0.86	0.028	0.034	
J	0.73	1.02	0.029	0.040	
K	12.70	14.73	0.500	0.580	
L	6.35		0.250		
M	45°BSC		45°	BSC	
N	5.08	BSC	0.200	BSC	
P		1.27		0.050	
R	1.37 BSC		0.054	0.054 BSC	
T		0.76		0.030	
U	2.54		0.100		

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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